

Jun Suda

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

270 papers	3,856 citations	33 h-index	48 g-index
304 ext. papers	4,382 ext. citations	1.9 avg, IF	5.71 L-index

#	Paper	IF	Citations
270	Dependence of Electrical Characteristics on Epitaxial Layer Structure of AlGaIn/GaN HEMTs Fabricated on Freestanding GaN Substrates. <i>IEEE Transactions on Electron Devices</i> , 2022 , 69, 88-95	2.9	1
269	Identification of type of threading dislocation causing reverse leakage in GaN p-n junctions after continuous forward current stress.. <i>Scientific Reports</i> , 2022 , 12, 1458	4.9	1
268	Hole traps related to nitrogen displacement in p-type GaN grown by metalorganic vapor phase epitaxy on freestanding GaN. <i>Applied Physics Letters</i> , 2022 , 120, 142104	3.4	0
267	Effect of annealing time and pressure on electrical activation and surface morphology of Mg-implanted GaN annealed at 1300 °C in ultra-high-pressure nitrogen ambient. <i>Applied Physics Express</i> , 2021 , 14, 121004	2.4	6
266	Effect of Schottky barrier height on quantitative analysis of deep-levels in n-type GaN by deep-level transient spectroscopy. <i>AIP Advances</i> , 2021 , 11, 115124	1.5	1
265	Enhanced activation of Mg ion-implanted GaN at decreasing annealing temperature by prolonging duration. <i>Applied Physics Express</i> , 2021 , 14, 011005	2.4	8
264	Breakdown Electric Field of GaN p+-n and p-n+ Junction Diodes with Various Doping Concentrations. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	1
263	Mg-implanted bevel edge termination structure for GaN power device applications. <i>Applied Physics Letters</i> , 2021 , 118, 093502	3.4	11
262	Isochronal annealing study of Mg-implanted p-type GaN activated by ultra-high-pressure annealing. <i>Applied Physics Express</i> , 2021 , 14, 056501	2.4	7
261	Impact ionization coefficients and critical electric field in GaN. <i>Journal of Applied Physics</i> , 2021 , 129, 185702	7.0	23
260	Increase of reverse leakage current at homoepitaxial GaN p-n junctions induced by continuous forward current stress. <i>Applied Physics Letters</i> , 2021 , 118, 253501	3.4	5
259	Design and demonstration of nearly-ideal edge termination for GaN pB junction using Mg-implanted field limiting rings. <i>Applied Physics Express</i> , 2021 , 14, 074002	2.4	8
258	Electrical characteristics of gated-anode diodes based on normally-off GaN HEMT structures for rectenna applications. <i>Electronics Letters</i> , 2021 , 57, 810	1.1	0
257	Impact of gamma-ray irradiation on capacitance-voltage characteristics of Al ₂ O ₃ /GaN MOS diodes with and without post-metallization annealing. <i>Applied Physics Express</i> , 2021 , 14, 015501	2.4	0
256	Design guidelines suppressing dynamic punch-through in GaN vertical MOSFETs by considering the Poole-Frenkel effect. <i>Applied Physics Express</i> , 2021 , 14, 024001	2.4	
255	Fabrication of GaN cantilever on GaN substrate by photo-electrochemical etching. <i>Applied Physics Express</i> , 2021 , 14, 036505	2.4	0
254	Formation of highly vertical trenches with rounded corners via inductively coupled plasma reactive ion etching for vertical GaN power devices. <i>Applied Physics Letters</i> , 2021 , 118, 102101	3.4	6

253	Impact of channel mobility on design optimization of 600B300V-class high-speed GaN vertical-trench MOSFETs based on TCAD simulation. <i>Applied Physics Express</i> , 2021 , 14, 094002	2.4	0
252	Fabrication of 150-nm AlGaIn/GaN field-plated High Electron Mobility Transistors using i-line stepper. <i>Electronics Letters</i> , 2021 , 57, 948	1.1	
251	Depth profiles of electron traps generated during reactive ion etching in n-type 4H-SiC characterized by using isothermal capacitance transient spectroscopy. <i>Journal of Applied Physics</i> , 2021 , 130, 105703	2.5	1
250	Nitrogen-displacement-related electron traps in n-type GaN grown on a GaN freestanding substrate. <i>Applied Physics Letters</i> , 2021 , 118, 012106	3.4	8
249	Electron traps formed by gamma-ray irradiation in homoepitaxial n-type GaN and their annealing behavior. <i>AIP Advances</i> , 2020 , 10, 045023	1.5	5
248	Identification of origin of E C 0.6 eV electron trap level by correlation with iron concentration in n-type GaN grown on GaN freestanding substrate by metalorganic vapor phase epitaxy. <i>Applied Physics Express</i> , 2020 , 13, 071007	2.4	14
247	Defect evolution in Mg ions implanted GaN upon high temperature and ultrahigh N ₂ partial pressure annealing: Transmission electron microscopy analysis. <i>Journal of Applied Physics</i> , 2020 , 127, 105106	2.5	20
246	Temperature Dependence of Conductivity Modulation in SiC Bipolar Junction Transistors. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 1699-1704	2.9	3
245	Dual-color-sub-bandgap-light-excited isothermal capacitance transient spectroscopy for quick measurement of carbon-related hole trap density in n-type GaN. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SGGD05	1.4	1
244	Why do electron traps at E C 0.6 eV have inverse correlation with carbon concentrations in n-type GaN layers?. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 105505	1.4	10
243	Depth profiling of surface damage in n-type GaN induced by inductively coupled plasma reactive ion etching using photo-electrochemical techniques. <i>Applied Physics Express</i> , 2020 , 13, 106505	2.4	3
242	Improvement of channel property of GaN vertical trench MOSFET by compensating nitrogen vacancies with nitrogen plasma treatment. <i>Applied Physics Express</i> , 2020 , 13, 124003	2.4	7
241	Effects of Dosage Increase on Electrical Properties of Metal-Oxide-Semiconductor Diodes with Mg-Ion-Implanted GaN Before Activation Annealing. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900367	1.3	5
240	Overview of carrier compensation in GaN layers grown by MOVPE: toward the application of vertical power devices. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SA0804	1.4	19
239	Reduction of plasma-induced damage in n-type GaN by multistep-bias etching in inductively coupled plasma reactive ion etching. <i>Applied Physics Express</i> , 2020 , 13, 016505	2.4	15
238	Redistribution of Mg and H atoms in Mg-implanted GaN through ultra-high-pressure annealing. <i>Applied Physics Express</i> , 2020 , 13, 086501	2.4	18
237	Impact of Film Stress of Field-Plate Dielectric on Electric Characteristics of GaN-HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 5421-5426	2.9	7
236	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. <i>Scientific Reports</i> , 2020 , 10, 17349	4.9	9

235	Progress on and challenges of p-type formation for GaN power devices. <i>Journal of Applied Physics</i> , 2020 , 128, 090901	2.5	30
234	Impacts of high temperature annealing above 1400°C under N ₂ overpressure to activate acceptors in Mg-implanted GaN 2020 ,		4
233	Franz-Keldysh effect in 4H-SiC p ⁺ n junction diodes under high electric field along the $\langle 11\bar{2}0 \rangle$ direction. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 091007	1.4	2
232	Electric-field-induced simultaneous diffusion of Mg and H in Mg-doped GaN prepared using ultra-high-pressure annealing. <i>Applied Physics Express</i> , 2019 , 12, 111005	2.4	19
231	Demonstration of Conductivity Modulation in SiC Bipolar Junction Transistors With Reduced Base Spreading Resistance. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4870-4874	2.9	5
230	Acceptors activation of Mg-ion implanted GaN by ultra-high-pressure annealing 2019 ,		2
229	Highly effective activation of Mg-implanted p-type GaN by ultra-high-pressure annealing. <i>Applied Physics Letters</i> , 2019 , 115, 142104	3.4	58
228	Measurement of avalanche multiplication utilizing Franz-Keldysh effect in GaN p-n junction diodes with double-side-depleted shallow bevel termination. <i>Applied Physics Letters</i> , 2019 , 115, 142101	3.4	14
227	Design and Fabrication of GaN p-n Junction Diodes With Negative Beveled-Mesa Termination. <i>IEEE Electron Device Letters</i> , 2019 , 40, 941-944	4.4	45
226	Estimation of Impact Ionization Coefficient in GaN by Photomultiplication Measurement Utilizing Franz-Keldysh Effect 2019 ,		2
225	Shockley-Read-Hall lifetime in homoepitaxial p-GaN extracted from recombination current in GaN p ⁺ n junction diodes. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCB14	1.4	12
224	Deep-level transient spectroscopy studies of electron and hole traps in n-type GaN homoepitaxial layers grown by quartz-free hydride-vapor-phase epitaxy. <i>Applied Physics Letters</i> , 2019 , 115, 012103	3.4	28
223	Impact Ionization Coefficients in GaN Measured by Above- and Sub-Eg Illuminations for p ⁺ n Junction 2019 ,		15
222	A comparative study on electrical characteristics of 1-kV pnp and npn SiC bipolar junction transistors. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 04FR04	1.4	3
221	Sources of carrier compensation in metalorganic vapor phase epitaxy-grown homoepitaxial n-type GaN layers with various doping concentrations. <i>Applied Physics Express</i> , 2018 , 11, 041001	2.4	41
220	Accurate method for estimating hole trap concentration in n-type GaN via minority carrier transient spectroscopy. <i>Applied Physics Express</i> , 2018 , 11, 071002	2.4	16
219	Phonon-assisted optical absorption due to Franz-Keldysh effect in 4H-SiC p ⁺ n junction diode under high reverse bias voltage. <i>Applied Physics Express</i> , 2018 , 11, 091302	2.4	7
218	Analytical formula for temperature dependence of resistivity in p-type 4H-SiC with wide-range doping concentrations. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 088002	1.4	4

217	Effects of Parasitic Region in SiC Bipolar Junction Transistors on Forced Current Gain. <i>Materials Science Forum</i> , 2018 , 924, 629-632	0.4	4
216	Determination of Surface Recombination Velocity From Current-Voltage Characteristics in SiC p-n Diodes. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4786-4791	2.9	3
215	Impacts of Finger Numbers on ON-State Characteristics in Multifinger SiC BJTs With Low Base Spreading Resistance. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2771-2777	2.9	4
214	Characterization of carrier concentration and mobility of GaN bulk substrates by Raman scattering and infrared reflectance spectroscopies. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 070309	1.4	0
213	Franz-Keldysh effect in GaN p-n junction diode under high reverse bias voltage. <i>Applied Physics Letters</i> , 2018 , 112, 252104	3.4	13
212	Hall-effect measurements of metalorganic vapor-phase epitaxy-grown p-type homoepitaxial GaN layers with various Mg concentrations. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 031001	1.4	46
211	Temperature dependence of barrier height in Ni/n-GaN Schottky barrier diode. <i>Applied Physics Express</i> , 2017 , 10, 051002	2.4	29
210	Interface properties of NO-annealed 4H-SiC (0001), (1120), and (1100) MOS structures with heavily doped p-bodies. <i>Journal of Applied Physics</i> , 2017 , 121, 145703	2.5	9
209	Reduction of interface state density in SiC (0001) MOS structures by post-oxidation Ar annealing at high temperature. <i>AIP Advances</i> , 2017 , 7, 045008	1.5	15
208	Effect of Postoxidation Nitridation on Forward Current-Voltage Characteristics in 4H-SiC Mesa p-n Diodes Passivated With SiO ₂ . <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3016-3018	2.9	4
207	Electrical properties of n- and p-type 4H-SiC formed by ion implantation into high-purity semi-insulating substrates. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 070306	1.4	18
206	Design Criterion for SiC BJTs to Avoid ON-Characteristics Degradation Due to Base Spreading Resistance. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2086-2091	2.9	6
205	Ultrahigh-Voltage SiC MPS Diodes With Hybrid Unipolar/Bipolar Operation. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 874-881	2.9	24
204	Correlation between shapes of Shockley stacking faults and structures of basal plane dislocations in 4H-SiC epilayers. <i>Philosophical Magazine</i> , 2017 , 97, 2736-2752	1.6	22
203	ESR Study on Hydrogen Passivation of Intrinsic Defects in p-Type and Semi-Insulating 4H-SiC. <i>Materials Science Forum</i> , 2016 , 858, 318-321	0.4	2
202	Modeling of surface roughness scattering in nanowires based on atomistic wave function: Application to hole mobility in rectangular germanium nanowires. <i>Physical Review B</i> , 2016 , 93,	3.3	4
201	Strong impact of the initial III/V ratio on the crystalline quality of an AlN layer grown by rf-plasma-assisted molecular-beam epitaxy. <i>Applied Physics Express</i> , 2016 , 9, 025502	2.4	6
200	Promise and Challenges of High-Voltage SiC Bipolar Power Devices. <i>Energies</i> , 2016 , 9, 908	3.1	26

- 199 Strain control in AlN top layer by inserting an ultrathin GaN interlayer on an AlN template coherently grown on SiC(0001) by PAMBE. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 814-818 1.3 2
- 198 Hall-effect measurements of metalorganic vapor-phase epitaxy-grown p-type homoepitaxial GaN layers with various Mg concentrations. *Japanese Journal of Applied Physics*, **2016**, 55, 05FH03 1.4 2
- 197 Control of carrier lifetime of thick n-type 4H-SiC epilayers by high-temperature Ar annealing. *Applied Physics Express*, **2016**, 9, 061303 2.4 27
- 196 Interface state density of SiO₂/p-type 4H-SiC (0001), (112 $\bar{0}$ 0), (11 $\bar{0}$ 00) metal-oxide-semiconductor structures characterized by low-temperature subthreshold slopes. *Applied Physics Letters*, **2016**, 108, 152108 3.4 24
- 195 Analysis of High-Field Hole Transport in Germanium and Silicon Nanowires Based on Boltzmann's Transport Equation. *IEEE Nanotechnology Magazine*, **2016**, 1-1 2.6 2
- 194 Analysis of ballistic and quasi-ballistic hole transport properties in germanium nanowires based on an extended Γ op of the Barrier model. *Solid-State Electronics*, **2016**, 123, 143-149 1.7 2
- 193 Hall scattering factors in p-type 4H-SiC with various doping concentrations. *Applied Physics Express*, **2016**, 9, 041301 2.4 22
- 192 Surface passivation on 4H-SiC epitaxial layers by SiO₂with POCl₃annealing. *Applied Physics Express*, **2016**, 9, 051301 2.4 10
- 191 Franz-Keldysh effect in n-type GaN Schottky barrier diode under high reverse bias voltage. *Applied Physics Express*, **2016**, 9, 091002 2.4 6
- 190 Interface Properties of 4H-SiC ($\{11\bar{2}0\}$) and ($\{1\bar{1}00\}$) MOS Structures Annealed in NO. *IEEE Transactions on Electron Devices*, **2015**, 62, 309-315 2.9 52
- 189 Impact Ionization Coefficients in 4H-SiC Toward Ultrahigh-Voltage Power Devices. *IEEE Transactions on Electron Devices*, **2015**, 62, 3326-3333 2.9 53
- 188 Influence of Conduction-Type on Thermal Oxidation Rate in SiC(0001) with Various Doping Densities. *Materials Science Forum*, **2015**, 821-823, 456-459 0.4 1
- 187 High-Temperature Operation of Electrostatically-Excited Single-Crystalline 4H-SiC Microcantilever Resonators. *Materials Science Forum*, **2015**, 821-823, 914-918 0.4
- 186 Ultrahigh-Voltage SiC p-i-n Diodes With Improved Forward Characteristics. *IEEE Transactions on Electron Devices*, **2015**, 62, 374-381 2.9 88
- 185 Oxidation-induced majority and minority carrier traps in n- and p-type 4H-SiC. *Applied Physics Express*, **2015**, 8, 111301 2.4 7
- 184 Temperature dependence of forward characteristics for ultrahigh-voltage SiC p \bar{n} diodes with a long carrier lifetime. *Japanese Journal of Applied Physics*, **2015**, 54, 098004 1.4 6
- 183 Temperature dependence of current gain in 4H-SiC bipolar junction transistors. *Japanese Journal of Applied Physics*, **2015**, 54, 04DP13 1.4 7
- 182 Phonon-Limited Electron Mobility in Rectangular Cross-Sectional Ge Nanowires. *IEEE Transactions on Electron Devices*, **2014**, 61, 1993-1998 2.9 9

181	100 mm diameter mono-crystalline 4H-SiC/polycrystalline-SiC bonded wafers fabricated by SAB for power device 2014 ,		1
180	. <i>IEEE Electron Device Letters</i> , 2014 , 35, 339-341	4.4	10
179	Decay curve analyses in carrier lifetime measurements of p- and n-type 4H-SiC epilayers. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 111301	1.4	4
178	Identification of dislocations in 4H-SiC epitaxial layers and substrates using photoluminescence imaging. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 020304	1.4	21
177	Ion implantation technology in SiC for power device applications 2014 ,		19
176	Formation mechanism of threading-dislocation array in AlN layers grown on 6H-SiC (0001) substrates with 3-bilayer-high surface steps. <i>Applied Physics Letters</i> , 2014 , 105, 071603	3.4	12
175	Temperature Dependence of Impact Ionization Coefficients in 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 461-466	0.4	19
174	Impact of conduction type and doping density on thermal oxidation rate of SiC(0001). <i>Applied Physics Express</i> , 2014 , 7, 121301	2.4	4
173	Effect of ultrathin AlN spacer on electronic properties of GaN/SiC heterojunction bipolar transistors. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 034101	1.4	16
172	Quantitative comparison between Z1 Σ center and carbon vacancy in 4H-SiC. <i>Journal of Applied Physics</i> , 2014 , 115, 143705	2.5	33
171	Conduction-type dependence of thermal oxidation rate on SiC(0001) 2014 ,		1
170	Etching-limiting process and origin of loading effects in silicon etching with hydrogen chloride gas. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 016502	1.4	2
169	Ultrahigh-Voltage (> 20 kV) SiC PiN Diodes with a Space-Modulated JTE and Lifetime Enhancement Process via Thermal Oxidation. <i>Materials Science Forum</i> , 2014 , 778-780, 832-835	0.4	14
168	Fabrication of Electrostatically Actuated 4H-SiC Microcantilever Resonators by Using n/p/n Epitaxial Structures and Doping-Selective Electrochemical Etching. <i>Materials Science Forum</i> , 2014 , 778-780, 780-783	0.4	1
167	Designing of Quasi-Modulated Region in 4H-SiC Lateral RESURF MOSFETs. <i>Materials Science Forum</i> , 2014 , 778-780, 943-946	0.4	1
166	Identification of the Negative Carbon Vacancy at Quasi-Cubic Site in 4H-SiC by EPR and Theoretical Calculations. <i>Materials Science Forum</i> , 2014 , 778-780, 285-288	0.4	
165	Enhancement of carrier lifetime in lightly Al-doped p-type 4H-SiC epitaxial layers by combination of thermal oxidation and hydrogen annealing. <i>Applied Physics Express</i> , 2014 , 7, 085501	2.4	23
164	Temperature dependence of optical absorption coefficient of 4H- and 6H-SiC from room temperature to 300 °C. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 108003	1.4	8

163	Orientation and Shape Effects on Ballistic Transport Properties in Gate-All-Around Rectangular Germanium Nanowire nFETs. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 944-950	2.9	9
162	AlGaN/SiC Heterojunction Bipolar Transistors Featuring AlN/GaN Short-Period Superlattice Emitter. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 2768-2775	2.9	3
161	Deep levels generated by thermal oxidation in p-type 4H-SiC. <i>Journal of Applied Physics</i> , 2013 , 113, 033705	2.9	14
160	Coherent Growth of AlN/GaN Short-Period Superlattice with Average GaN Mole Fraction of up to 20% on 6H-SiC(0001) Substrates by Plasma-Assisted Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JE21	1.4	3
159	Effects of Nitridation on 4H-SiC MOSFETs Fabricated on Various Crystal Faces. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1260-1262	2.9	48
158	Single-crystalline 4H-SiC micro cantilevers with a high quality factor. <i>Sensors and Actuators A: Physical</i> , 2013 , 197, 122-125	3.9	14
157	Long Photoconductivity Decay Characteristics in p-Type 4H-SiC Bulk Crystals. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 010202	1.4	7
156	Optical Properties of Highly Strained AlN Coherently Grown on 6H-SiC(0001). <i>Applied Physics Express</i> , 2013 , 6, 062604	2.4	9
155	Persistent Photoconductivity in p-Type 4H-SiC Bulk Crystals. <i>Materials Science Forum</i> , 2013 , 740-742, 413-416	0.4	1
154	Improvement of Carrier Lifetimes in Highly Al-Doped p-Type 4H-SiC Epitaxial Layers by Hydrogen Passivation. <i>Applied Physics Express</i> , 2013 , 6, 121301	2.4	15
153	Ultrahigh-Voltage SiC PiN Diodes with an Improved Junction Termination Extension Structure and Enhanced Carrier Lifetime. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 070204	1.4	6
152	Deep Levels Generated by Thermal Oxidation in n-Type 4H-SiC. <i>Applied Physics Express</i> , 2013 , 6, 051301	2.4	9
151	Growth, Electrical Characterization, and Electroluminescence of GaN/SiC Heterojunction Diodes and Bipolar Transistors Fabricated on SiC Off-Axis Substrates. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 124102	1.4	2
150	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. <i>Applied Physics Letters</i> , 2013 , 102, 112106	3.4	44
149	Space-Modulated Junction Termination Extension for Ultrahigh-Voltage p-i-n Diodes in 4H-SiC. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 414-418	2.9	76
148	Breakdown characteristics of 1200 kV-class 4H-SiC PiN diodes with improved junction termination structures 2012 ,		9
147	21-kV SiC BJTs With Space-Modulated Junction Termination Extension. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1598-1600	4.4	82
146	Thermo-Optic Coefficients of 4H-SiC, GaN, and AlN for Ultraviolet to Infrared Regions up to 500 °C. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 112101	1.4	5

145	Breakdown Characteristics of 15-kV-Class 4H-SiC PiN Diodes With Various Junction Termination Structures. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 2748-2752	2.9	33
144	Over-700-nm Critical Thickness of AlN Grown on 6H-SiC(0001) by Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 105502	2.4	25
143	AlN/GaN Short-Period Superlattice Coherently Grown on 6H-SiC(0001) Substrates by Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 051002	2.4	3
142	On the Formation of Intrinsic Defects in 4H-SiC by High Temperature Annealing Steps. <i>Materials Science Forum</i> , 2012 , 717-720, 247-250	0.4	4
141	Enhanced Current Gain (>250) in 4H-SiC Bipolar Junction Transistors by a Deep-Level-Reduction Process. <i>Materials Science Forum</i> , 2012 , 717-720, 1117-1122	0.4	9
140	Experimental Study on Various Junction Termination Structures Applied to 15 kV 4H-SiC PiN Diodes. <i>Materials Science Forum</i> , 2012 , 717-720, 973-976	0.4	4
139	Elimination of Deep Levels in Thick SiC Epilayers by Thermal Oxidation and Proposal of the Analytical Model. <i>Materials Science Forum</i> , 2012 , 717-720, 241-246	0.4	5
138	21.7 kV 4H-SiC PiN Diode with a Space-Modulated Junction Termination Extension. <i>Applied Physics Express</i> , 2012 , 5, 064001	2.4	56
137	Carrier Recombination in n-Type 4H-SiC Epilayers with Long Carrier Lifetimes. <i>Applied Physics Express</i> , 2012 , 5, 101301	2.4	43
136	Current Transport Characteristics of Quasi-Al _x Ga _{1-x} N/SiC Heterojunction Bipolar Transistors with Various Band Discontinuities. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 04DP09	1.4	1
135	Growth of Nitrogen-Polar 2H-AlN on Step-Height-Controlled 6H-SiC($\bar{1}\bar{1}\bar{1}$) Substrate by Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 02BH02	1.4	1
134	Doping-Induced Lattice Mismatch and Misorientation in 4H-SiC Crystals. <i>Materials Science Forum</i> , 2012 , 717-720, 481-484	0.4	22
133	High temperature annealing of n-type 4H-SiC: Impact on intrinsic defects and carrier lifetime. <i>Journal of Applied Physics</i> , 2012 , 111, 033515	2.5	43
132	4H-SiC pn Photodiodes with Temperature-Independent Photoresponse up to 300 $^{\circ}$ C. <i>Applied Physics Express</i> , 2012 , 5, 094101	2.4	21
131	Analytical model for reduction of deep levels in SiC by thermal oxidation. <i>Journal of Applied Physics</i> , 2012 , 111, 053710	2.5	57
130	Growth of Nitrogen-Polar 2H-AlN on Step-Height-Controlled 6H-SiC(0001) Substrate by Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 02BH02	1.4	2
129	Current Transport Characteristics of Quasi-Al _x Ga _{1-x} N/SiC Heterojunction Bipolar Transistors with Various Band Discontinuities. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 04DP09	1.4	1
128	Thermo-Optic Coefficients of 4H-SiC, GaN, and AlN for Ultraviolet to Infrared Regions up to 500 $^{\circ}$ C. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 112101	1.4	12

127	Epitaxial Growth and Defect Control of SiC for High-Voltage Power Devices. <i>Journal of the Vacuum Society of Japan</i> , 2011 , 54, 362-368		2
126	Thermo-optic coefficients of SiC, GaN, and AlN up to 512°C from infrared to ultraviolet region for tunable filter applications 2011 ,		2
125	Fabrication of electrostatic-actuated single-crystalline 4H-SiC bridge structures by photoelectrochemical etching 2011 ,		4
124	Anomalously low Ga incorporation in high Al-content AlGaIn grown on $\{11\bar{2}0\}$ non-polar plane by molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 1498-1500	1.6	2
123	4H-SiC BJTs With Record Current Gains of 257 on (0001) and 335 on $\{000\}\bar{1}$. <i>IEEE Electron Device Letters</i> , 2011 , 32, 841-843	4.4	43
122	Improvement of Current Gain in 4H-SiC BJTs by Surface Passivation With Deposited Oxides Nitrided in N_2O or NO. <i>IEEE Electron Device Letters</i> , 2011 , 32, 285-287	4.4	30
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120	Origin of Etch Hillocks Formed on On-Axis SiC(000 $\bar{1}$) Surfaces by Molten KOH Etching. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 038002	1.4	2
119	Nonradiative recombination at threading dislocations in 4H-SiC epilayers studied by micro-photoluminescence mapping. <i>Journal of Applied Physics</i> , 2011 , 110, 033525	2.5	18
118	4H-SiC bipolar junction transistors with record current gains of 257 on (0001) and 335 on (000 $\bar{1}$) 2011 ,		9
117	Reduction of Threading Dislocation Density in 2H-AlN Grown on 6H-SiC(0001) by Minimizing Unintentional Active-Nitrogen Exposure before Growth. <i>Applied Physics Express</i> , 2011 , 4, 025502	2.4	23
116	Impact of Carrier Lifetimes on Non-Destructive Mapping of Dislocations in 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2011 , 679-680, 302-305	0.4	1
115	Improved Current Gain in 4H-SiC BJTs Passivated with Deposited Oxides Followed by Nitridation. <i>Materials Science Forum</i> , 2011 , 679-680, 698-701	0.4	
114	Improved Characteristics of SiC MOSFETs by Post-Oxidation Annealing in Ar at High Temperature. <i>Materials Science Forum</i> , 2011 , 679-680, 445-448	0.4	5
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103	Temperature and Injection Level Dependencies of Carrier Lifetimes in p-Type and n-Type 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2010 , 645-648, 199-202	0.4	2
102	Electrical Characterization and Reliability of Nitrided-Gate Insulators for N- and P-Type 4H-SiC MIS Devices. <i>Materials Science Forum</i> , 2010 , 645-648, 825-828	0.4	2
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3	Lifetime-Killing Defects in 4H-SiC Epilayers and Lifetime Control by Low-Energy Electron Irradiation	267-286	1
2	4H-SiC MISFETs with Nitrogen-Containing Insulators	235-265	2

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